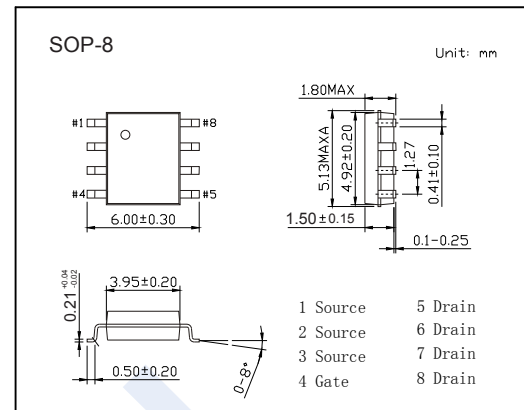


P-Channel MOSFET

KI10P40DY

■ Features

- $V_{DS} = -40V$
- $I_D = -15A$
- $R_{DS(on)} = 42m\Omega @ V_{GS} = -10V, I_D = -1A$
- $R_{DS(on)} = 70m\Omega @ V_{GS} = -4.5V, I_D = -1A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_A = 25^\circ C$ -15	A
		$T_A = 70^\circ C$ -10	
Pulsed Drain Current	I_{DM}	-30	
Power Dissipation	P_D	$T_A = 25^\circ C$ 1.3	W
		$T_A = 70^\circ C$ 0.8	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -32V, V_{GS} = 0V, T_J = 25^\circ C$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -1A$			42	m Ω
		$V_{GS} = -10V, I_D = -10A$			45	
		$V_{GS} = -4.5V, I_D = -1A$			70	

■ Marking

Marking	10P40 KC****
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